NP0A456

Silicon PNP epitaxial planar type

For High speed switching

Features

- Suitable for high-density mounting and downsizing of the equipment
- Automatic insertion with the taping is possible

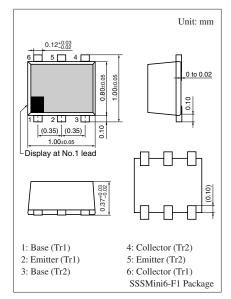
Basic Part Number

• $2SA2082 \times 2$

Absolute Maximum Ratings $T_a = 25^{\circ}C$

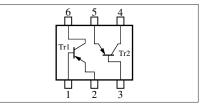
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-15	V	
Collector-emitter voltage (Base open)	V _{CEO}	-15	V	
Emitter-base voltage (Collector open)	V _{EBO}	-4	V	
Collector current	I _C	-50	mA	
Peak collector current	I _{CP}	-100	mA	
Total power dissipation *	P _T	125	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	

Note) *: Measuring on substrate at 17 mm \times 10 mm \times 1 mm



Marking Symbol: 3E

Internal Connection

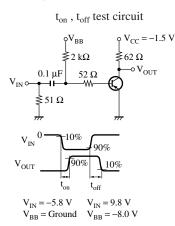


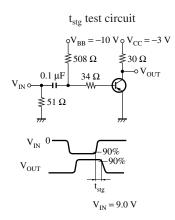
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -8 V, I_E = 0$			- 0.1	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -3 V, I_C = 0$			- 0.1	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -1 V, I_C = -10 mA$	50		150	_
	h _{FE2}	$V_{CE} = -1 V, I_C = -1 mA$	30			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$		- 0.1	- 0.2	V
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	800	1 500		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -5 V, I_E = 0, f = 1 MHz$		1		pF
Turn-on time	t _{on}	Refer to the switching time measurement circuit		12		ns
Turn-off time	t _{off}			20		ns
Storage time	t _{stg}			19		ns

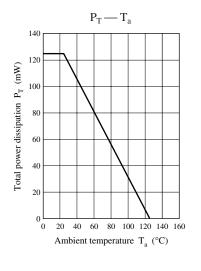
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

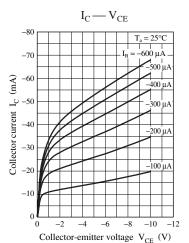
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

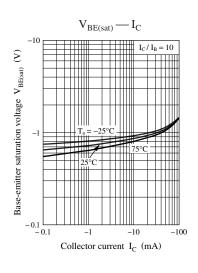
Switching time measurement circuit

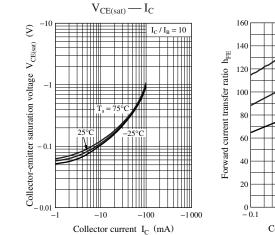


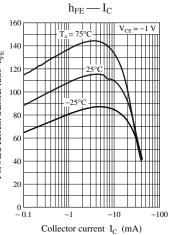


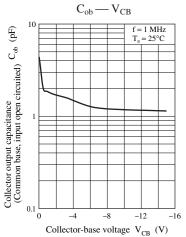












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